

EAST - [10749500.wsp:1]

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Search: L1: Browse: Active: Query: DBs: US-PG-PUB, US-PAT, EPO, JPO ☐ Flush Default operator: OR ☒ Highlight all full term matches

ferroelectric near polymer and sputter\$3

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PR5 form AS&B form Image Doc HTML

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20040256948 A1	20041223	14	Electronic device formed from a thin film with vertically oriented columns with an insulating filler material	310/311	
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20040256649 A1	20041223	10	Ferroelectric memory device with a conductive polymer layer and a method of formation	257/295	257/209; 257/910; 438/128
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20040217402 A1	20041104	10	Ferroelectric memory device with a conductive polymer layer and a method of formation	257/296	
7	<input type="checkbox"/>	<input type="checkbox"/>	US 20040209420 A1	20041021	11	Method for making a ferroelectric memory cell in a ferroelectric memory device, and a ferroelectric memory device	438/239	
8	<input type="checkbox"/>	<input type="checkbox"/>	US 20040160819 A1	20040819	30	High-density NVRAM	365/171	
9	<input type="checkbox"/>	<input type="checkbox"/>	US 20040137712 A1	20040715	7	Interlayer connections for layered electronic devices	438/622	
10	<input type="checkbox"/>	<input type="checkbox"/>	US 20040114913 A1	20040617	74	Optical recording an or reproducing apparatus optical reproducing apparatus optical recording and or reproducing means optical recording and or reproducing means	386/125	386/126
11	<input type="checkbox"/>	<input type="checkbox"/>	US 20040109298 A1	20040610	17	Dielectric material including particulate filler	361/762	156/306.9
12	<input type="checkbox"/>	<input type="checkbox"/>	US 20040102054 A1	20040527	8	Method of removing edge bead during the manufacture of an integrated circuit	438/778	257/E21.255; 257/E21.264; 438/71
13	<input type="checkbox"/>	<input type="checkbox"/>	US 20040002176 A1	20040101	17	Organic ferroelectric memory cells	438/40	257/40
14	<input type="checkbox"/>	<input type="checkbox"/>	US 20030179617 A1	20030925	16	Ferroelectric or electret memory circuit	365/200	257/E27.071

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